



BFL4036 — N-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- ON-resistance $R_{DS(on)}=0.4\Omega$ (typ.)
- Input capacitance $C_{iss}=1000\text{pF}$ (typ.)
- 10V drive

Specifications

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		500	V
Gate-to-Source Voltage	V_{GSS}		± 30	V
Drain Current (DC)	I_{Dc}^{*1}	Limited only by maximum temperature $T_{ch}=150^\circ\text{C}$	14	A
	I_{Dpack}^{*2}	$T_c=25^\circ\text{C}$ (SANYO's ideal heat dissipation condition)*3	9.6	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu\text{s}$, duty cycle $\leq 1\%$	50	A
Allowable Power Dissipation	P_D		2.0	W
		$T_c=25^\circ\text{C}$ (SANYO's ideal heat dissipation condition)*3	37	W
Channel Temperature	T_{ch}		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^\circ\text{C}$
Avalanche Energy (Single Pulse) *4	E_{AS}		122	mJ
Avalanche Current *5	I_{AV}		14	A

Note : *1 Shows chip capability

*2 Package limited

*3 SANYO's condition is radiation from backside.

The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.

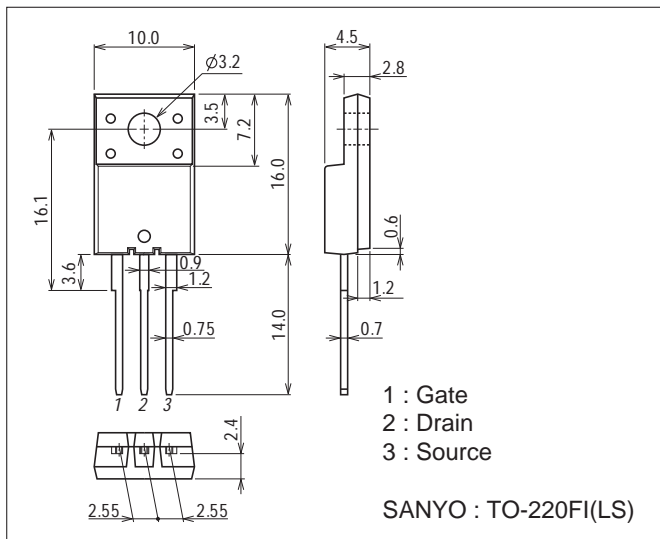
*4 $V_{DD}=99\text{V}$, $L=1\text{mH}$, $I_{AV}=14\text{A}$ (Fig.1)

*5 $L \leq 1\text{mH}$, single pulse

Package Dimensions

unit : mm (typ)

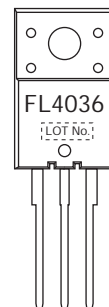
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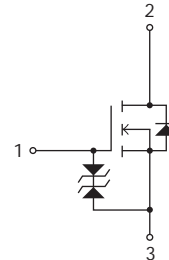
Product & Package Information

- Package : TO-220FI(LS)
- JEITA, JEDEC : SC-67, SOT-186A, TO-220F
- Minimum Packing Quantity : 100 pcs./bag or 50pcs./magazine

Marking



Electrical Connection



Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=10mA, V_{GS}=0V$	500			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=400V, V_{GS}=0V$			100	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 24V, V_{DS}=0V$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10V, I_D=1mA$	3		5	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10V, I_D=7A$	3.5	7		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)}$	$I_D=7A, V_{GS}=10V$		0.4	0.52	Ω
Input Capacitance	C_{iss}	$V_{DS}=30V, f=1MHz$		1000		pF
Output Capacitance	C_{oss}	$V_{DS}=30V, f=1MHz$		200		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS}=30V, f=1MHz$		44		pF
Turn-ON Delay Time	$t_{d(on)}$	See Fig.2		22		ns
Rise Time	t_r	See Fig.2		66		ns
Turn-OFF Delay Time	$t_{d(off)}$	See Fig.2		117		ns
Fall Time	t_f	See Fig.2		46		ns
Total Gate Charge	Q_g	$V_{DS}=200V, V_{GS}=10V, I_D=14A$		38.4		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS}=200V, V_{GS}=10V, I_D=14A$		6.7		nC
Gate-to-Drain "Miller" Charge	Q_{gd}	$V_{DS}=200V, V_{GS}=10V, I_D=14A$		22.1		nC
Diode Forward Voltage	V_{SD}	$I_S=14A, V_{GS}=0V$		0.95	1.3	V
Reverse Recovery Time	t_{rr}	See Fig.3		520		ns
Reverse Recovery Charge	Q_{rr}	$I_S=14A, V_{GS}=0V, di/dt=100A/\mu s$		4200		nC

Fig.1 Avalanche Resistance Test Circuit

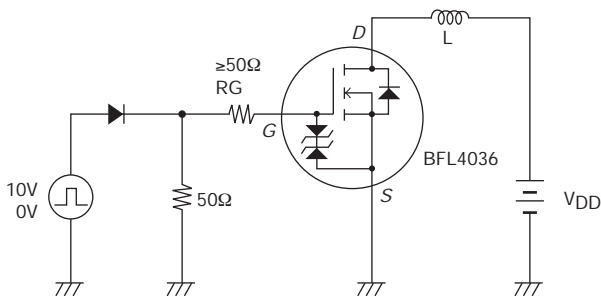


Fig.2 Switching Time Test Circuit

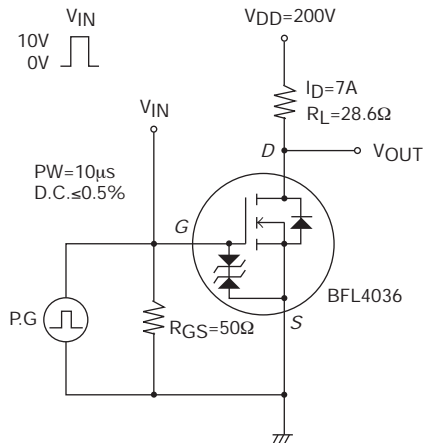
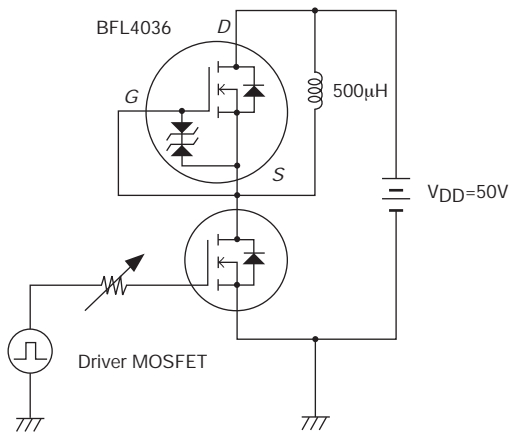
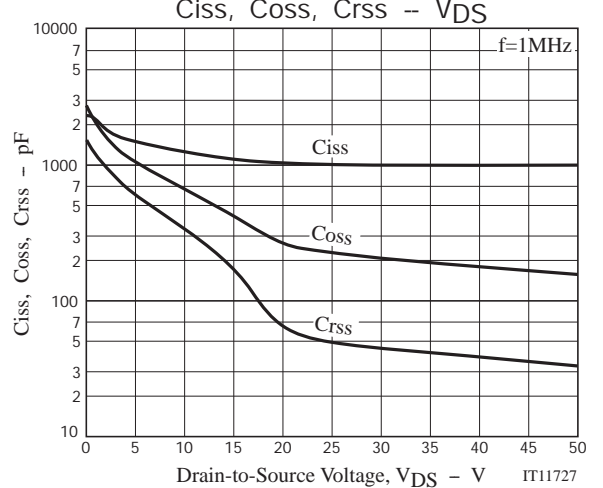
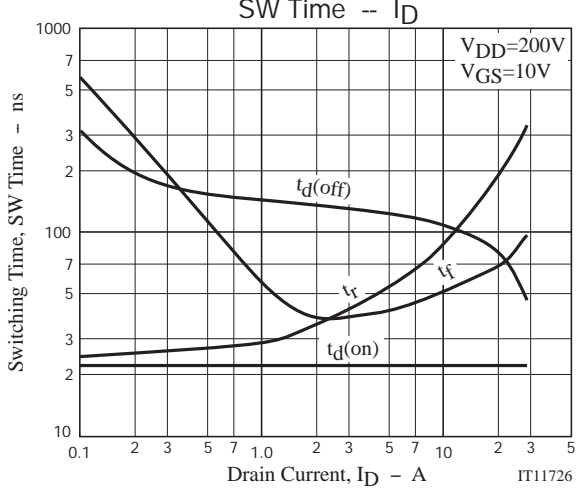
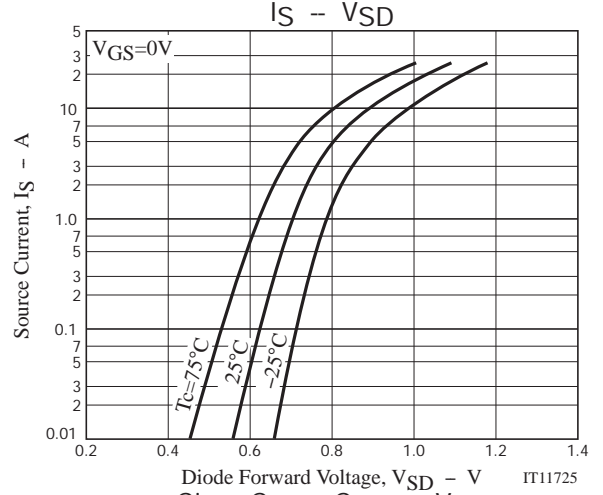
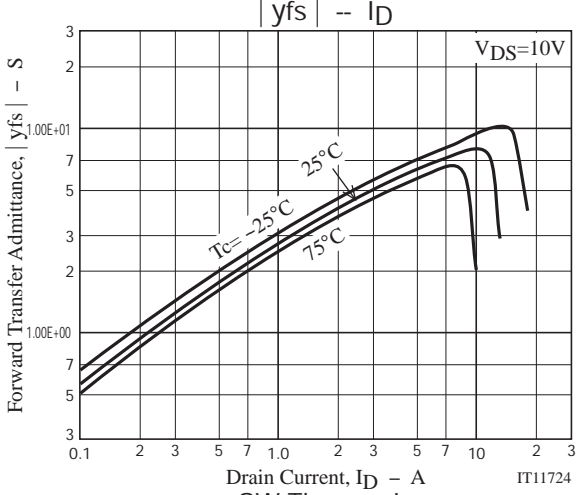
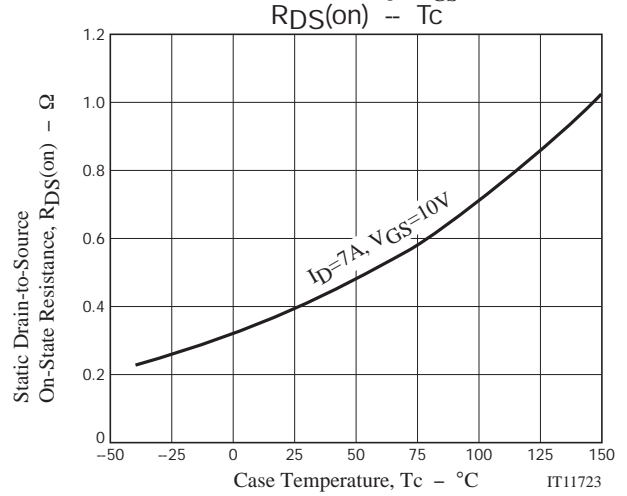
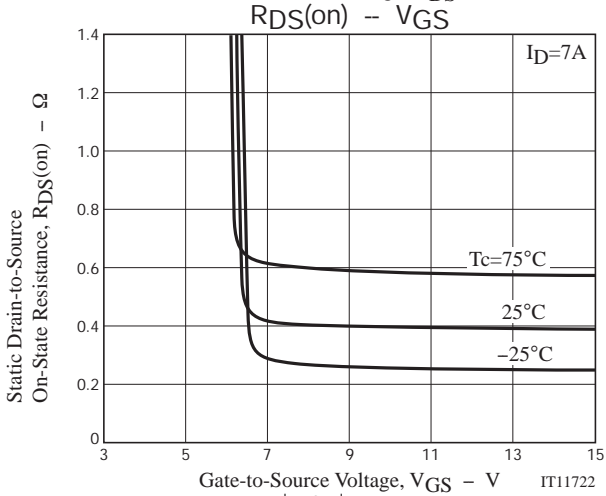
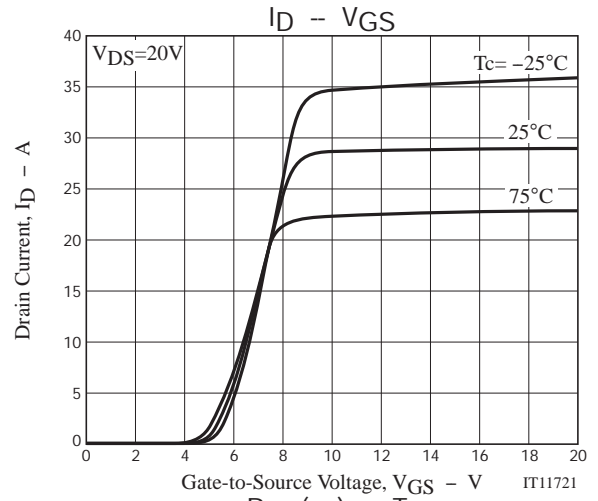
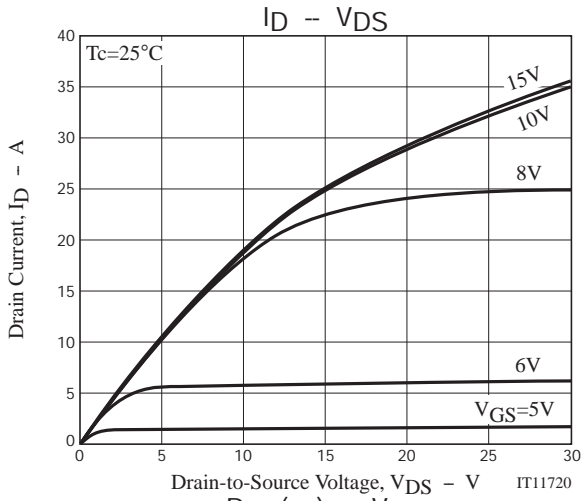
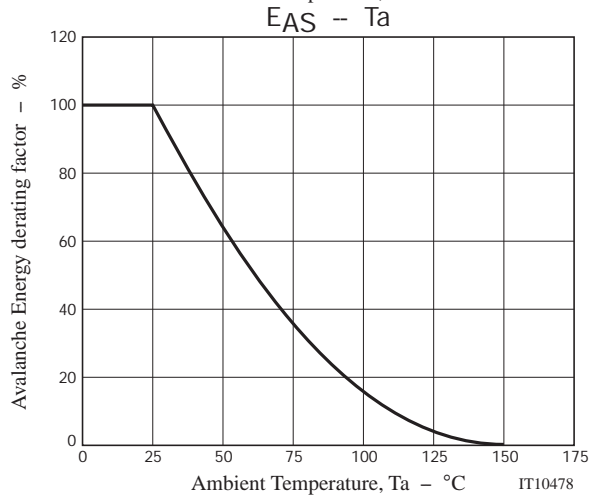
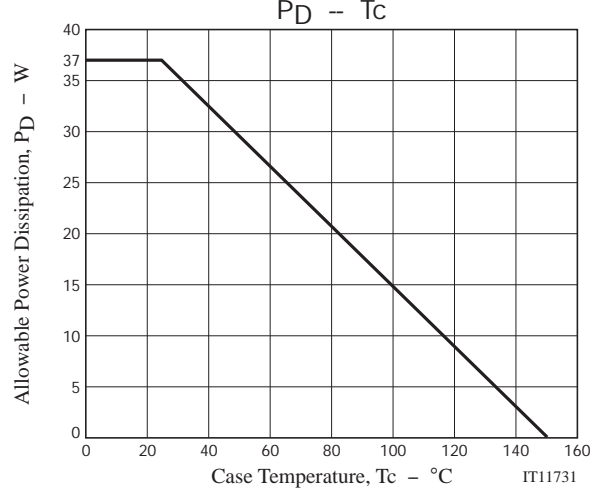
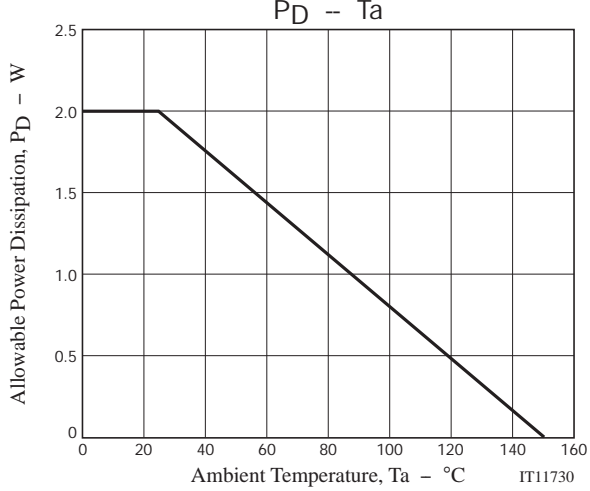
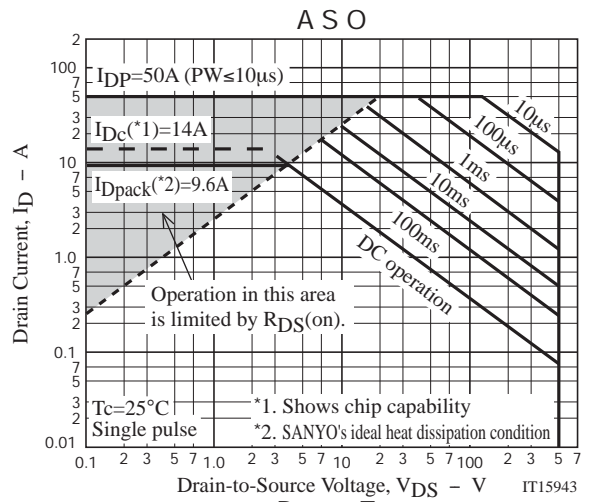
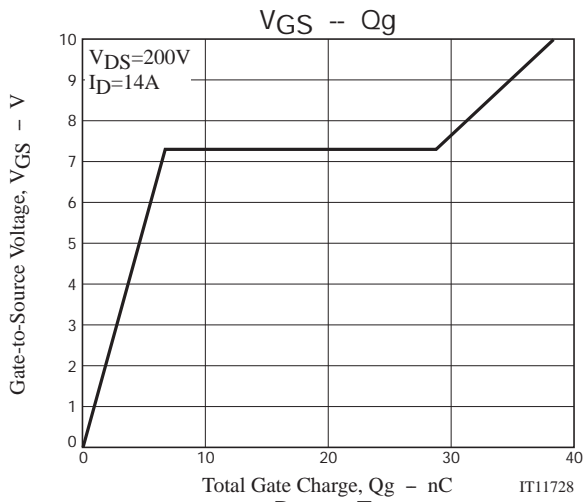


Fig.3 Reverse Recovery Time Test Circuit







Note on usage : Since the BFL4036 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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